Silicon NPN Power Transistors MJW21192

DESCRIPTION

·With TO-247 package
·Complement to type MJW21191
·Wild area of safe operation

APPLICATIONS

·Designed for power audio output, high power drivers in audio amplifiers

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

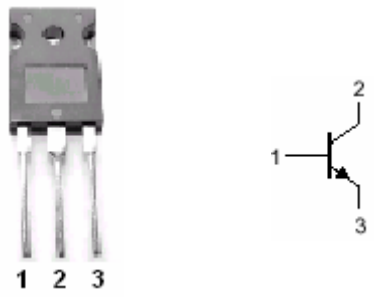

Fig.1 simplified outline (TO-247) and symbol

ABSOLUTE MAXIMUM RATINGS(Tc=25□)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_{CBO}	Collector-base voltage	Open emitter	150	V
V_{CEO}	Collector-emitter voltage	Open base	150	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		8	A
I_{CM}	Collector current-peak		16	A
I_B	Base current		2	A
P_D	Total power dissipation	T_C=25□	100	W
T_j	Junction temperature		-65~150	□
T_{stg}	Storage temperature		-65~150	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j\text{-}C}$	Thermal resistance from junction to case	0.65	□/W

CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=10mA ;I_B=0	150			V
$V_{CE(sat)-1}$	Collector-emitter saturation voltage	I_C=4A; I_B=0.4A			1.0	V
$V_{CE(sat)-2}$	Collector-emitter saturation voltage	I_C=8A; I_B=1.6A			2.0	V
$V_{BE(ON)}$	Base-emitter on voltage	I_C=4A ; V_{CE}=2V			2.0	V
I_{CES}	Collector cut-off current	V_{CB}=150V; I_E=0			10	μA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			10	μA
h_{FE-1}	DC current gain	I_C=4A ; V_{CE}=2V	15		100	
h_{FE-2}	DC current gain	I_C=8A ; V_{CE}=2V	5			
f_T	Transition frequency	I_C=1.0A ; V_{CE}=10V,f=1MHz	4.0			MHz

PACKAGE OUTLINE

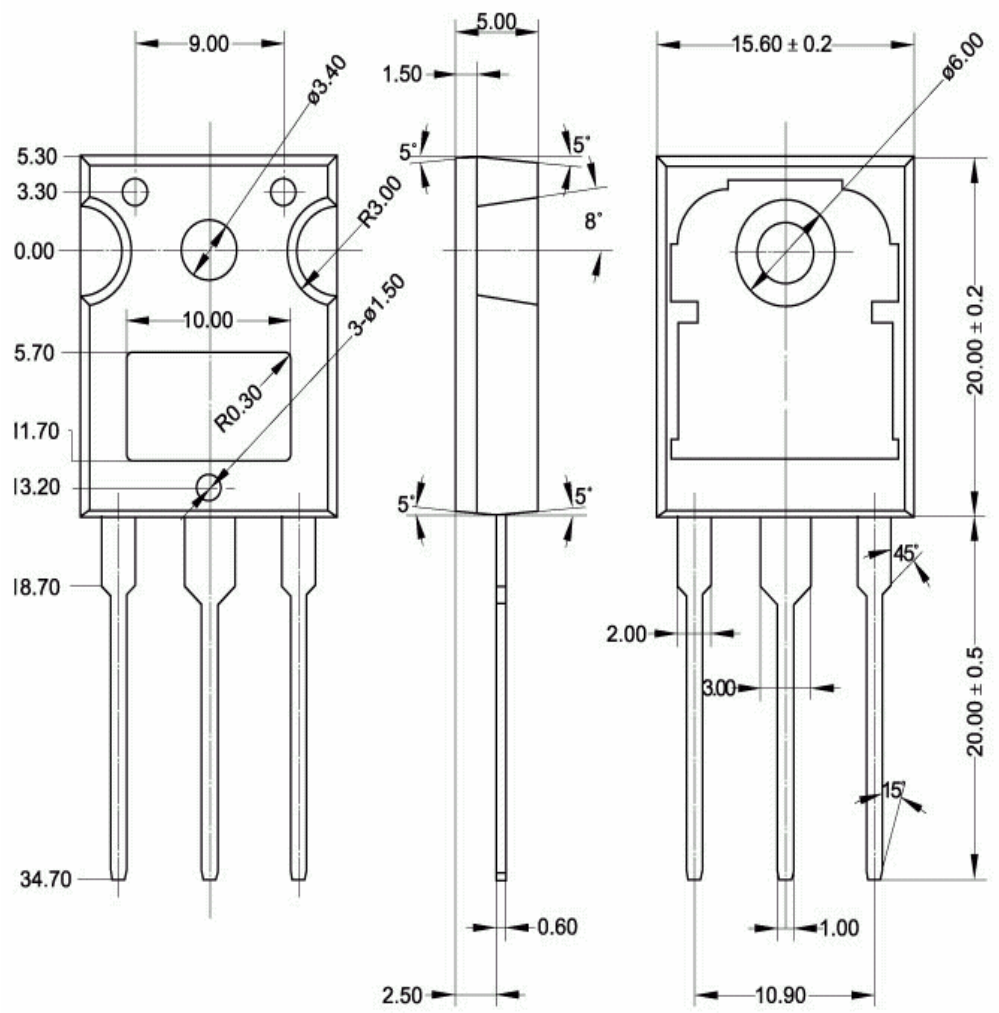

Fig.2 Outline dimensions